

Silicon PNP Power Transistors

2SA1492

DESCRIPTION

- With TO-3PN package
- Complement to type 2SC3856

APPLICATIONS

- Audio and general purpose

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

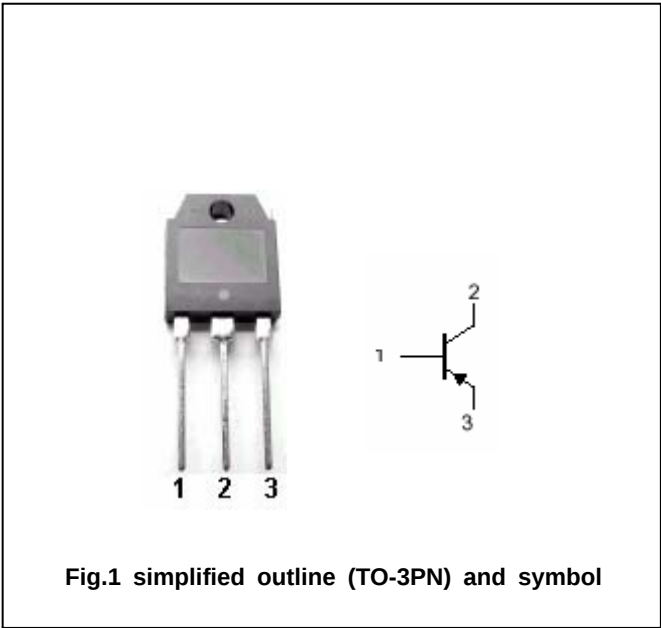


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-180	V
V_{CEO}	Collector-emitter voltage	Open base	-180	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-15	A
I_B	Base current		-4	A
P_C	Collector power dissipation	$T_C=25$	130	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

Silicon PNP Power Transistors

2SA1492

CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -50mA$; $I_B = 0$	-180			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -5A$; $I_B = -0.5A$			-2.0	V
I_{CBO}	Collector cut-off current	$V_{CB} = -180V$; $I_E = 0$			-100	μA
I_{EBO}	Emitter cut-off current	$V_{EB} = -6V$; $I_C = 0$			-100	μA
h_{FE}	DC current gain	$I_C = -3A$; $V_{CE} = -4V$	50		180	
C_{OB}	Output capacitance	$I_E = 0$; $V_{CB} = 10V, f = 1MHz$		500		pF
f_T	Transition frequency	$I_C = -0.5A$; $V_{CE} = -12V$		20		MHz

Switching times

t_{on}	Turn-on time	$I_C = -10A$; $R_L = 4\Omega$ $I_{B1} = -I_{B2} = -1A$ $V_{CC} = 40V$		0.60		μs
t_s	Storage time			0.90		μs
t_f	Fall time			0.20		μs

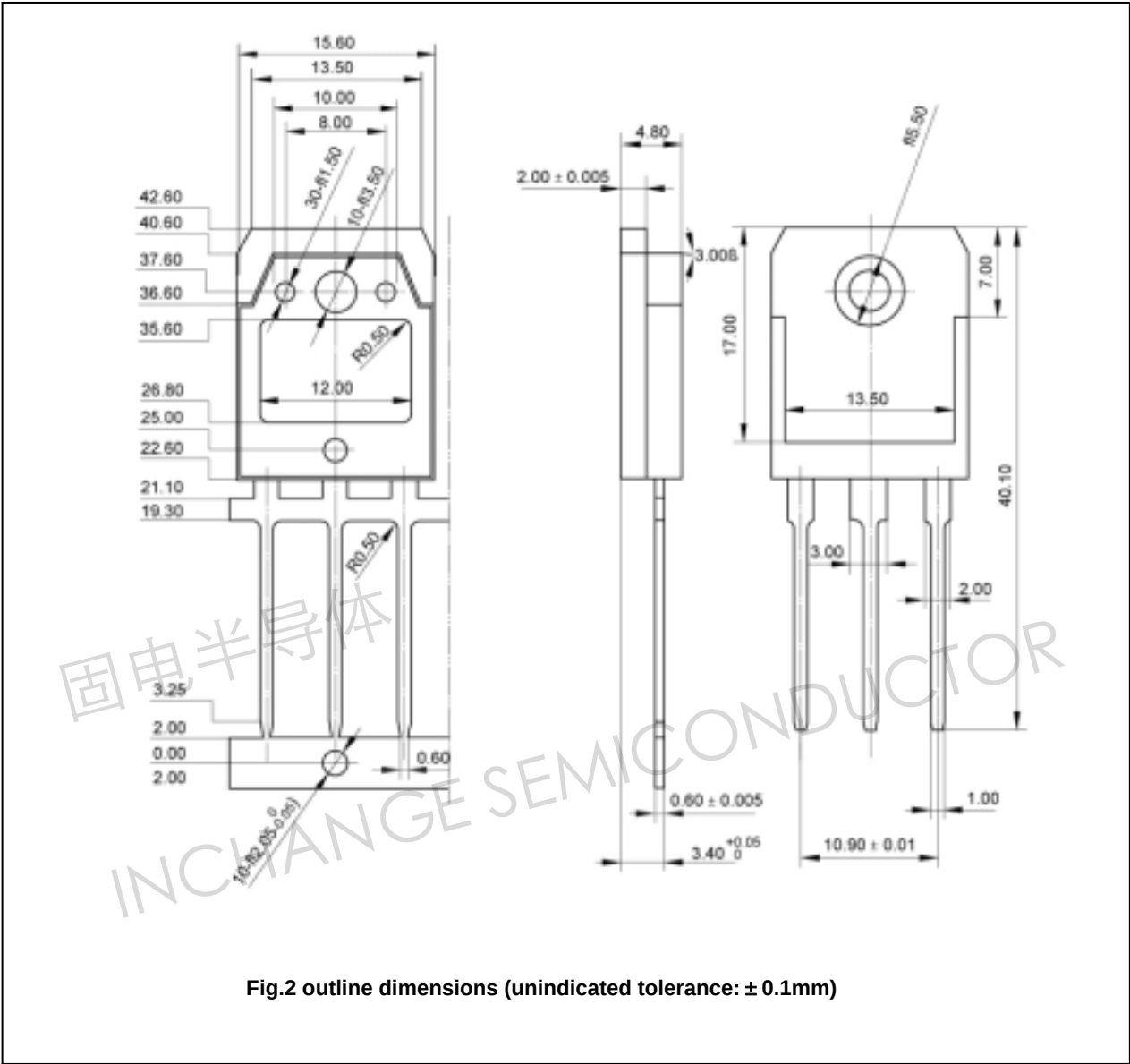
◆ h_{FE} Classifications

O	P	Y
50-100	70-140	90-180

Silicon PNP Power Transistors

2SA1492

PACKAGE OUTLINE



Silicon PNP Power Transistors

2SA1492

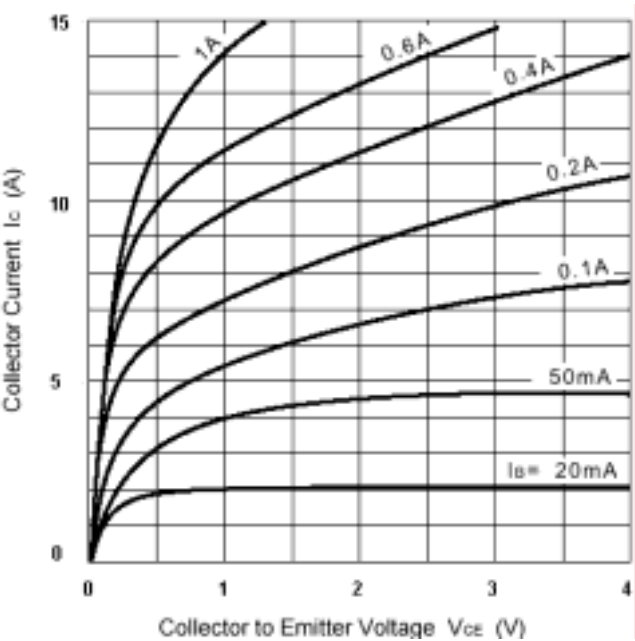


Fig.3 Static Characteristic

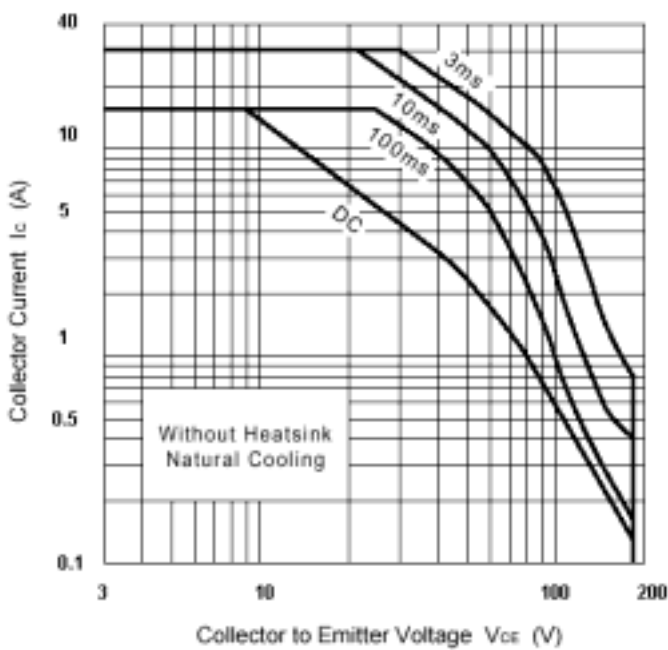


Fig.4 Safe Operating Area

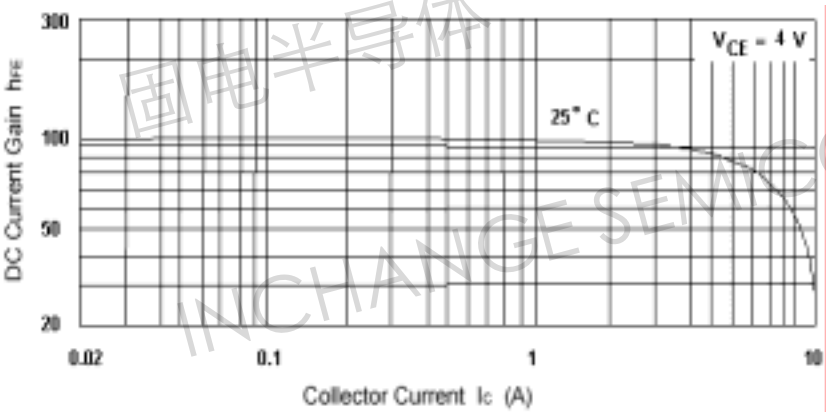


Fig.5 DC current Gain